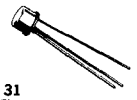
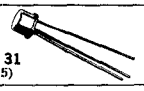
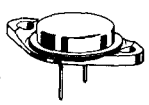
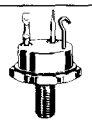
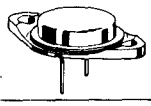
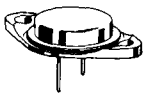
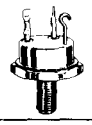
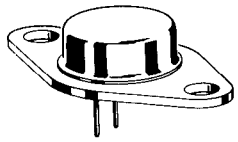
TYPE	MATERIAL	POLARITY	REPLACEMENT	PAGE NUMBER	USE	MAXIMUM RATINGS						ELECTRICAL CHARACTERISTICS									
						P_D @ 25°C	Ref Point	T_J °C	V_{CB} (volts)	V_{CE-} (volts)	Subscript	h_{FE} @ I_C (min)	(max)	Units	$V_{CE(SAT)}$ @ I_C (volts)	Units	h_{f-}	Subscript	f_- Units	Subscript
2N3766	S	N		7-142	LPA	20W	C	175	80	60	O	40	160	0.5A	2.5	1.0A	40	E	15M	T
2N3767	S	N		7-142	LPA	20W	C	175	100	80	O	40	160	0.5A	2.5	1.0A	40	E	15M	T
2N3770	G	P			RFA	50M	A	100	10	6.0	O	10	200	1.0M			10	E	100M	T
2N3771	S	N			LPA	150W	C	200	50	40	O	15	60	15A	2.0	15A	40	E	0.2M	T
2N3772	S	N	2N3715	7-125	LPA	150W	C	200	100	60	O	15	60	10A	1.4	10A	40	E	0.2M	T
2N3773	S	N			LPA	150W	C	200	160	140	O	15	60	8.0A	1.4	8.0A	40	E	0.2M	T
2N3774	S	P			PMS	5.0W	C	200	40	40	O	20	60	0.2A	0.2	0.2A			1.0M	T
2N3775	S	P			PMS	5.0W	C	200	60	60	O	20	60	0.2A	0.2	0.2A			1.0M	T
2N3776	S	P			PMS	5.0W	C	200	80	80	O	20	60	0.2A	0.2	0.2A			1.0M	T
2N3777	S	P			PMS	5.0W	C	200	100	100	O	20	60	0.2A	0.2	0.2A			1.0M	T
2N3778	S	P			PMS	5.0W	C	200	40	40	O	10	40	0.2A	0.2	0.2A			1.0M	T
2N3779	S	P			PMS	5.0W	C	200	60	60	O	10	40	0.2A	0.2	0.2A			1.0M	T
2N3780	S	P			PMS	5.0W	C	200	80	80	O	10	40	0.2A	0.2	0.2A			1.0M	T
2N3781	S	P			PMS	5.0W	C	200	100	100	O	10	40	0.2A	0.2	0.2A			1.0M	T
2N3782	S	P			PMS	5.0W	C	200	40	40	O	10	60	1.0A	0.75	1.0A			1.0M	T
2N3783	G	P		9-84	RFA	0.15W	A	100	30	20	O	20	200	3.0M	0.25	5.0M	20	E	0.8G	T
2N3784	G	P		9-84	RFA	0.15W	A	100	30	20	O	20	200	3.0M	0.25	5.0M	20	E	0.7G	T
2N3785	G	P		9-84	RFA	0.15W	A	100	15	12	O	15	200	3.0M	0.35	5.0M	15	E	0.7G	T
2N3788	S	N			LPA	100W	C	200	400	325	O	20	180	0.50A					50K	E
2N3789	S	P		7-147	LPA	150W	C	200	60	60	O	25	90	1.0A	1.0	5.0A	25	E	30K	E
2N3790	S	P		7-147	LPA	150W	C	200	60	80	O	25	90	1.0A	1.0	5.0A	25	E	30K	E
2N3791	S	P		7-147	LPA	150W	C	200	60	60	O	50	180	1.0A	1.0	5.0A	25	E	30K	E
2N3792	S	P		7-147	LPA	150W	C	200	80	80	O	50	180	1.0A	1.0	5.0A	25	E	30K	E
2N3793	S	N	MPS6530	5-118	AFA	0.25W	A	125	40	20	O	20	120	10M	0.4	10M			100M	T
2N3794	S	N	MPS6531	5-118	AFA	0.25W	A	125	40	20	O	100	600	10M	0.4	10M			100M	T
2N3795	S	P			PMS	5.0W	C	200	120	120	O	12	36	10M	0.2	10M			0.5M	T
2N3796																				
2N3797	Field Effect Transistors, see Table on Page 1-166																			
2N3798	S	P		8-278	AFA	0.36W	A	200	60	60	O	150	450	0.5M	0.2	0.1M	150	E	30M	T
2N3799	S	P		8-278	AFA	0.36W	A	200	60	60	O	300	900	0.5M	0.2		300	E	30M	T
2N3800	S	P		11-41	AFA	0.25W	A	200	60	60	O	150	450	0.1M	0.2	0.1M	150	E	100M	T
2N3801	S	P		11-41	AFA	0.25W	A	200	60	60	O	300	900	0.1M	0.2	0.1M	300	E	100M	T
2N3802	S	P		11-41	DFA	0.25W	A	200	60	60	O	150	450	0.1M	0.2	0.1M	150	E	100M	T
2N3803	S	P		11-41	DFA	0.25W	A	200	60	60	O	300	900	0.1M	0.2	0.1M	300	E	100M	T
2N3804	S	P		11-41	DFA	0.25W	A	200	60	60	O	150	450	0.1M	0.2	0.1M	150	E	100M	T
2N3805	S	P		11-41	DFA	0.25W	A	200	60	60	O	300	900	0.1M	0.2	0.1M	300	E	100M	T
2N3806	S	P		11-41	AFA	0.5W	A	200	60	60	O	150	450	0.1M	0.2	0.1M	150	E	100M	T
2N3807	S	P		11-41	AFA	0.5W	A	200	60	60	O	300	900	0.1M	0.2	0.1M	300	E	100M	T
2N3808	S	P		11-41	DFA	0.5W	A	200	60	60	O	150	450	0.1M	0.2	0.1M	150	E	100M	T
2N3809	S	P		11-41	DFA	0.5W	A	200	60	60	O	300	900	0.1M	0.2	0.1M	300	E	100M	T
2N3810	S	P		11-41	DFA	0.5W	A	200	60	60	O	150	450	0.1M	0.2	0.1M	150	E	100M	T
2N3811	S	P		11-41	DFA	0.5W	A	200	60	60	O	300	900	0.1M	0.2	0.1M	300	E	100M	T
2N3812	S	P		11-41	DFA	350M	A	200	60	60	O	150	450	0.1M	0.2	0.1M	150	E	100M	T
2N3813	S	P		11-41	DFA	350M	A	200	60	60	O	300	900	0.1M	0.2	0.1M	300	E	100M	T
2N3814	S	P		11-41	DFA	350M	A	200	60	60	O	150	450	0.1M	0.2	0.1M	150	E	100M	T
2N3815	S	P		11-41	DFA	350M	A	200	60	60	O	300	900	0.1M	0.2	0.1M	300	E	100M	T
2N3816	S	P		11-41	DFA	350M	A	200	60	60	O	150	450	0.1M	0.2	0.1M	150	E	100M	T
2N3817	S	P		11-41	DFA	350M	A	200	60	60	O	300	900	0.1M	0.2	0.1M	300	E	100M	T
2N3818	S	N		9-89	HPA	25W	C	175	60	60	S	5.0	50	400M	0.5	1.0A	3.0	E		
2N3819																				
thru	Field Effect Transistors, see Table on Page 1-166																			
2N3824																				
2N3825	S	N	MPS3398	5-86	RFC	0.25W	A	150	30	15	O	20		2.0M	0.25	2.0M			200M	T
2N3826	S	N	MPS3826	5-102	RFC	0.2W	A	150	60	45	O	40	160	10M					200M	T
2N3827	S	N	MPS3827	5-102	RFC	0.2W	A	150	60	45	O	100	400	10M					200M	T
2N3828	S	N	MPS6565	5-148	RFC	0.3W	A	150	40	40	O	30	200	12M					360M	T
2N3829	S	P			HSS	0.36W	A	200	35	20	O	30	120	30M	0.18	10M			350M	T
2N3830	S	N			HSS	1.0W	A	200	80	50	O	30		0.15A	0.3	0.15A			200M	T
2N3831	S	N			HSS	1.0W	A	200	70	40	O	35		0.15A	0.3	0.15A			200M	T
2N3832	S	N			HSS	0.2W	A	200	15	6.0	O	25	125	2.0M	0.4	10M			800M	T
2N3833	S	N			HPA				25	15	O	20		30M			2.5	E		
2N3834	S	N			HPA				25	15	O	20		30M			2.5	E		
2N3835	S	N			HPA				25	15	O	20		30M			2.5	E		
2N3836	S	N			PHS	1.0W	A	200	80	60	O	2K	20K	2.0A	1.8	5.0A			40M	T
2N3837	S	N			PHS	1.0W	A	200	100	80	O	2K	20K	2.0A	1.8	5.0A			40M	T
2N3838	S	N,P		11-45	HSA	0.25W	A	200	60	40	O	100	300	0.15A	0.4	0.15A	60	E	200M	T
2N3839	S	N			RFA	200M	A	200	30	15	O	30		3.0M					2.0G	T
2N3840	S	P			CHP	0.4W	A	200	50	50	O	30		0.2M	0.1	5.0M			6.0M	T
2N3841	S	P			CHP	0.3W	A	200	100	100	O	15		0.2M	0.12	5.0M			1.5M	T
2N3842	S	P			CHP	0.3W	A	200	120	120	O	10		1.0M		5.0M			1.0M	T
2N3843	S	N	MPS6512	5-109	RFC	0.2W	A	125	30	30	O	20	40	2.0M					60M	T
2N3843A	S	N	MPS6512	5-109	RFC	0.2W	A	125	30	30	O	20	40	2.0M					60M	T
2N3844	S	N	MPS6512	5-109	RFC	0.2W	A	125	30	30	O	35	70	2.0M					90M	T
2N3844A	S	N	MPS6512	5-109	RFC	0.2W	A	125	30	30	O	35	70	2.0M					90M	T
2N3845	S	N	MPS6512	5-109	RFC	0.2W	A	125	30	40	O	60	120	2.0M					126M	T
2N3845A	S	N	MPS6513	5-109	RFC	0.2W	A	125	30	30	O	60	120	2.0M					126M	T
2N3846	S	N			LPA	4.0W	A	175	300	200	O	10	60	10A	0.75	10A	50	E	10M	T
2N3847	S	N			LPA	4.0W	A	175	400	300	O	10	60	10A	0.75	10A	50	E	10M	T
2N3848	S	N			LPA	4.0W	A	175	300	300	O	10	60	15A	1.0	15A	50	E	10M	T
2N3849	S	N			LPA	4.0W	A	175	400	300	O	10	60	15A	1.0	15A	50	E	10M	T
2N3850	S	N			PHS	30W	C	200	100	80	O	50	150	1.0A	0.25	1.0A			20M	T
2N3851	S	N			PHS	30W	C	200	100	80	O	30	90	1.0A	0.25	1.0A			20M	T
2N3852	S	N			PHS	30W	C	200	60	40	O	50	150	1.0A	0.25	1.0A			20M	T
2N3853	S	N			PHS	30W	C	200	60	40	O	30	90	1.0A	0.25	1.0A			20M	T
2N3854	S	N	MPS6512	5-109	RFC	0.2W	A	150	18	18	O	35	70	2.0M					100M	T
2N3854A	S	N	MPS6512	5-109	RFC	0.2W	A	150	30	30	O	35	70	2.0M					100M	T
2N3855	S	N	MPS6512	5-109	RFC	0.2W	A	150	18	18	O	60	120	2.0M					130M	T
2N3855A	S	N	MPS6512	5-109	RFC	0.2W	A	150	30	30	O	60	120	2.0M					130M	T

SILICON POWER TRANSISTOR SELECTOR GUIDE (continued)

		Type NPN / PNP	V_{CEO} Volts (Max)	h_{FE} @ I_C Min/Max	I_C Amp	$V_{CE(sat)}$ @ I_C & I_B Volts (Max)	I_C Amp	I_B Amp
3.0 AMP ($T_{J(Max)}$ = 200°C)								
 Case 31 (TO-5) Solid Header	P_D = 6.0 W f_T — 3.0 MHz *f_T — 60 MHz	2N3719* 2N3720* 2N3867* 2N3868* 2N4234 2N4235 2N4236 2N4237 2N4238 2N4239	40 60 40 60 40 60 80 40 60 80	25/180 25/180 40/200 30/150 30/150 30/150 30/150 30/150 30/150 30/150	1.0 1.0 1.5 1.5 0.25 0.25 0.25 0.25 0.25 0.25	0.75 0.75 0.75 0.75 0.6 0.6 0.6 0.6 0.6 0.6	1.0 1.0 1.5 1.5 1.0 1.0 1.0 1.0 1.0 1.0	0.1 0.1 0.15 0.15 0.125 0.125 0.125 0.1 0.1 0.1
4.0 AMP ($T_{J(Max)}$ = 200°C)								
 Case 31 (TO-5)	P_D = 10 W f_T — 4.0 MHz	2N4877	60	20/100	4.0	1.0	4.0	0.4
 Case 80 (TO-66)	P_D = 20 W f_T — 10 MHz	2N3054* 2N3766 2N3767	60 60 80	25/100 40/160 40/160	0.5 0.5 0.5	1.0 1.0 1.0	0.5 0.5 0.5	0.05 0.05 0.05
	P_D = 25 W *f_T — 1.0 MHz f_T — 3.0 MHz **f_T — 4.0 MHz	2N3740 2N3741 2N4898 2N4899 2N4900 2N4910 2N4911 2N4912 MJ4101**	60 80 40 60 80 40 60 80 40	30/100 30/100 20/100 20/100 20/100 20/100 20/100 20/100 25/100	0.25 0.25 0.5 0.5 0.5 0.5 0.5 0.5 1.5	0.6 0.6 0.6 0.6 0.6 0.6 0.6 0.6 1.0	1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.0 1.5	0.125 0.125 0.1 0.1 0.1 0.1 0.1 0.1 0.15
	P_D = 35 W f_T — 1.0 MHz	2N4231 2N4232 2N4233	40 60 80	25/100 25/100 25/100	1.5 1.5 1.5	0.7 0.7 0.7	1.5 1.5 1.5	0.15 0.15 0.15
5.0 AMP ($T_{J(Max)}$ = 200°C)								
 Case 11 (TO-3)	P_D = 87.5 W f_T — 4.0 MHz	2N4901 2N4902 2N4903 2N4904 2N4905 2N4906	40 60 80 40 60 80	20/80 20/80 20/80 25/100 25/100 25/100	1.0 1.0 1.0 2.5 2.5 2.5	0.4 0.4 0.4 1.0 1.0 1.0	1.0 1.0 1.0 2.5 2.5 2.5	0.1 0.1 0.1 0.25 0.25 0.25
		2N4913 2N4914 2N4915 2N5067 2N5068 2N5069	40 60 80 40 60 80	25/100 25/100 25/100 20/80 20/80 20/80	2.5 2.5 2.5 1.0 1.0 1.0	1.0 1.0 1.0 0.4 0.4 0.4	2.5 2.5 2.5 1.0 1.0 1.0	0.25 0.25 0.25 0.1 0.1 0.1
 Case 9 (TO-61)	P_D = 117 W f_T — 10 MHz	2N1724 2N1725	80 80	20/90 50/150	2.0 2.0	1.0 1.0	2.0 2.0	0.2 0.2
7.5 AMP ($T_{J(Max)}$ = 200°C)								
 Case 11 (TO-3)	P_D = 115 W f_T — 10 MHz	2N3445 2N3446 2N3447 2N3448	60 80 60 80	20/60 20/60 40/120 40/120	3.0 3.0 5.0 5.0	1.5 1.5 1.5 1.5	3.0 3.0 5.0 5.0	0.3 0.3 0.5 0.5
 Case 1 (TO-3)	P_D = 117 W f_T — 1.0 MHz	2N3232	60	15/75	3.0	2.5	3.0	0.2
 Case 9 (TO-61)	P_D = 117 W f_T — 10 MHz	2N3487 2N3488 2N3489 2N3490 2N3491 2N3492	60 80 100 60 80 100	20/60 20/60 15/45 40/120 40/120 30/90	3.0 3.0 3.0 5.0 5.0 5.0	1.2 1.2 1.2 1.0 1.0 1.0	3.0 3.0 3.0 3.0 3.0 3.0	0.3 0.3 0.3 0.3 0.3 0.3

2N3766 (SILICON)
2N3767

V_{CB} = 80-100V
I_C = 4A
P_D = 20W



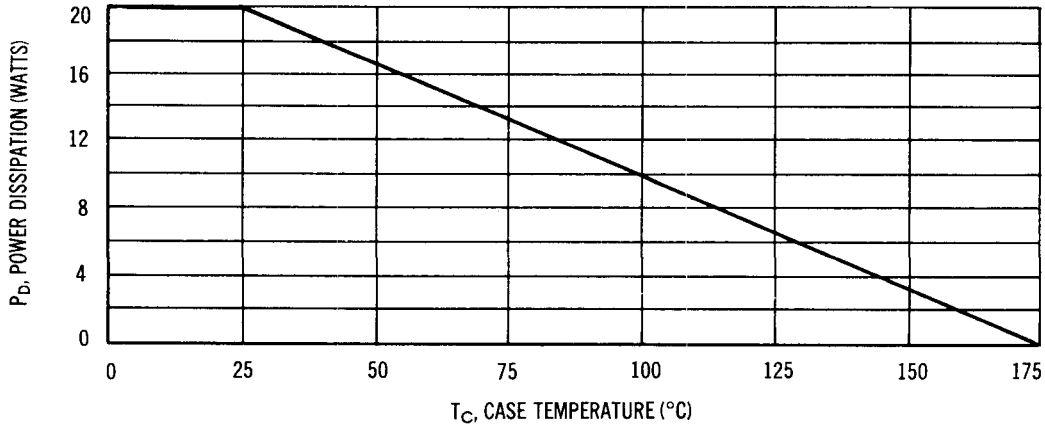
CASE 80
(TO-66)

Medium-power NPN silicon transistors, for use in switching, and medium-power-amplifier applications. Complement to PNP 2N3740 (2N3766) 2N3741 (2N3767).

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	2N3766	2N3767	Unit
Collector-Base Voltage	V_{CB}	80	100	Vdc
Emitter-Base Voltage	V_{EB}	6	6	Vdc
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector Current - Continuous	I_C	4.0		Adc
Peak		4.0		
Base Current	I_B	2.0		Adc
Total Device Dissipation @ T_C = 25° C	P_D	20		Watts
Derate above 25° C		0.133		W/°C
Thermal Resistance	θ_{JC}	7.5		°C/W
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to °175		°C

POWER-TEMPERATURE DERATING CURVE

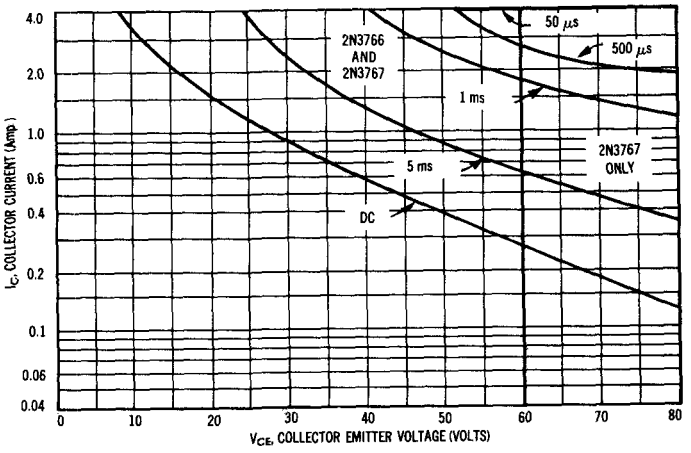


Safe area curves are indicated. Both limits are applicable and must be observed.

2N3766, 2N3767 (continued)

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise specified)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Voltage* (I_C = 100 mAdc, I_B = 0)	2N3766	BV_{CEO}*	60	—	Vdc
	2N3767		80	—	
Emitter-Base Cutoff Current (V_{EB} = 6 Vdc)		I_{EBO}	—	0.75	mAdc
Collector Cutoff Current		I_{CEX}			mAdc
(V_{CE} = 80 Vdc, V_{BE} = 1.5 Vdc)	2N3766		—	0.1	
(V_{CE} = 100 Vdc, V_{BE} = 1.5 Vdc)	2N3767		—	0.1	
(V_{CE} = 50 Vdc, V_{BE} = 1.5 Vdc, T_C = 150°C)	2N3766		—	1.0	
(V_{CE} = 70 Vdc, V_{BE} = 1.5 Vdc, T_C = 150°C)	2N3767		—	1.0	
Collector-Emitter Cutoff Current		I_{CEO}			mAdc
(V_{CE} = 60 Vdc, I_B = 0)	2N3766		—	0.7	
(V_{CE} = 80 Vdc, I_B = 0)	2N3767		—	0.7	
Collector-Base Cutoff Current		I_{CBO}			mAdc
(V_{CB} = 80 Vdc, I_E = 0)	2N3766		—	0.1	
(V_{CB} = 100 Vdc, I_E = 0)	2N3767		—	0.1	
ON CHARACTERISTICS					
DC Current Gain		h_{FE}			—
(I_C = 50 mAdc, V_{CE} = 5 Vdc)			30	—	
(I_C = 500 mAdc, V_{CE} = 5 Vdc)			40	160	
(I_C = 1.0 Adc, V_{CE} = 10 Vdc)			20	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$			Vdc
(I_C = 1 Adc, I_B = 0.1 Adc)			—	2.5	
(I_C = 500 mAdc, I_B = 50 mAdc)			—	1.0	
Base-Emitter Voltage (I_C = 1.0 Adc, V_{CE} = 10 Vdc)		V_{BE}	—	1.5	Vdc
TRANSIENT CHARACTERISTICS					
Current-Gain - Bandwidth Product (I_C = 500 mAdc, V_{CE} = 10 Vdc, f = 10 MHz)		f_T	15	—	MHz
Common-Base Output Capacitance (V_{CB} = 10 Vdc, I_C = 0 Adc, f = 100 kHz)		C_{ob}	—	50	pF
Small-Signal Current Gain (I_C = 100 mAdc, V_{CE} = 10 Vdc, f = 1 kHz)		h_{fe}	40	—	—



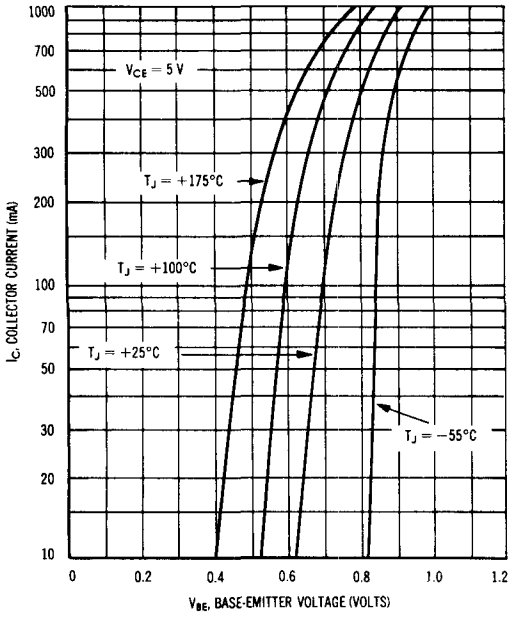
ACTIVE REGION SAFE AREAS

The Safe Operating Area Curves indicate I_C-V_{CE} limits below which the device will not go into secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a collector-emitter short. (Case temperature and duty cycle of the excursions make no significant change in these safe areas.) The load line may exceed the BV_{CEO} voltage limit only if the collector current has been reduced to 20 mA or less before or at the BV_{CES} limit; then and only then may the load line be extended to the absolute maximum voltage rating of BV_{CBO}. To insure operation below the maximum T_J, the power-temperature derating curve must be observed for both steady state and pulse power conditions.

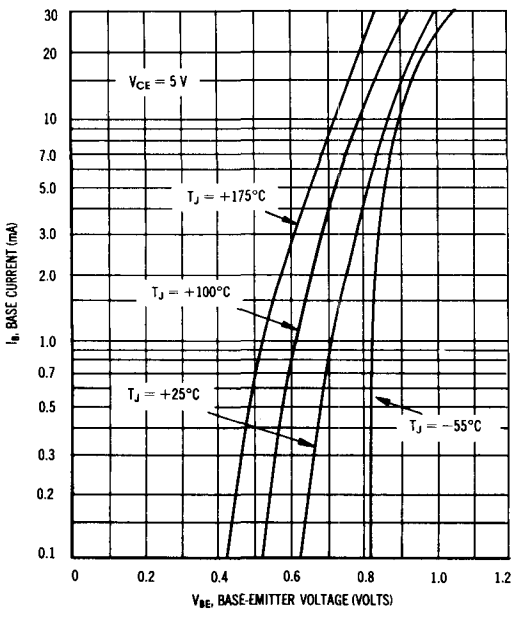
2N3766, 2N3767 (continued)

LARGE SIGNAL CHARACTERISTICS

TRANSCONDUCTANCE

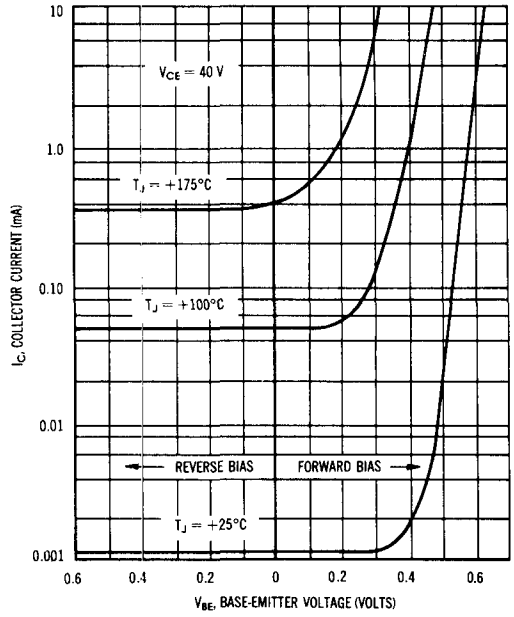


INPUT ADMITTANCE

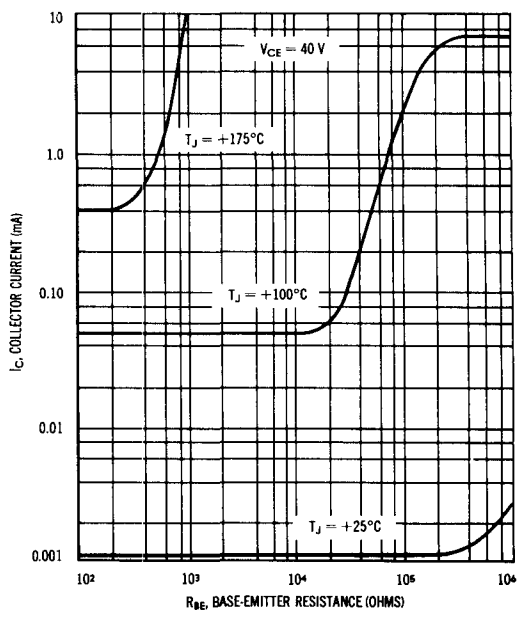


CUT-OFF CHARACTERISTICS

TRANSCONDUCTANCE

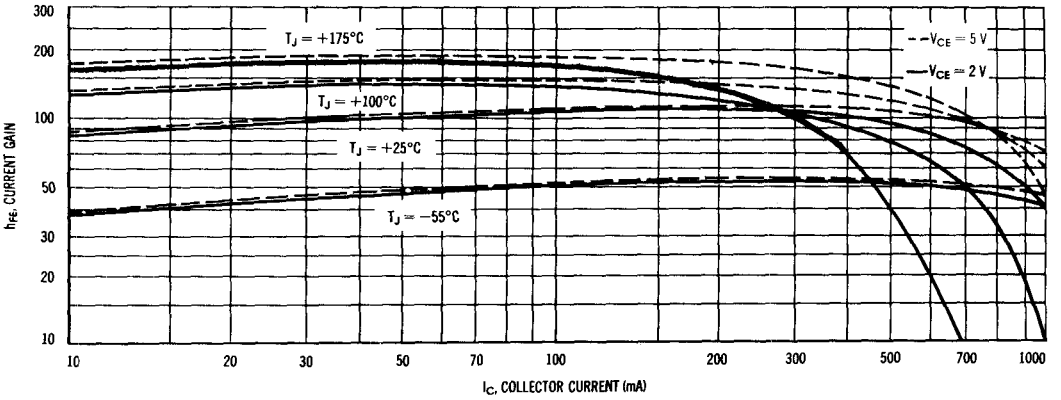


EFFECT OF BASE-EMITTER RESISTANCE

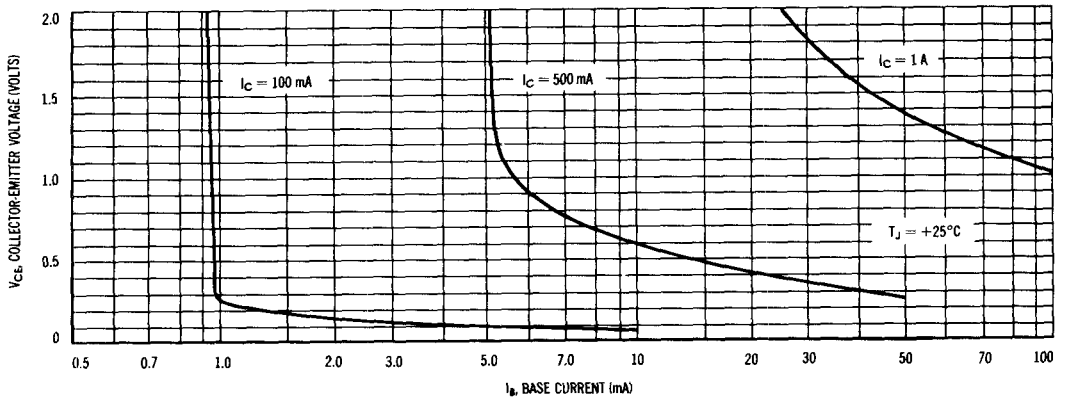


2N3766, 2N3767 (continued)

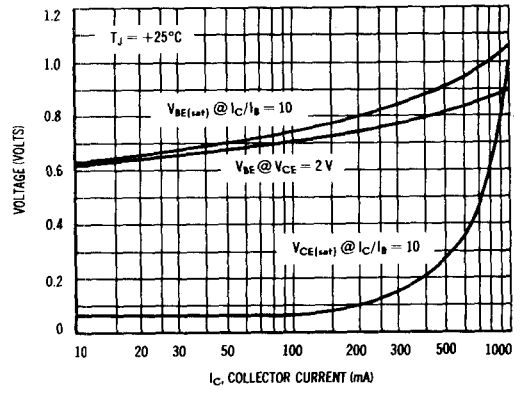
CURRENT GAIN



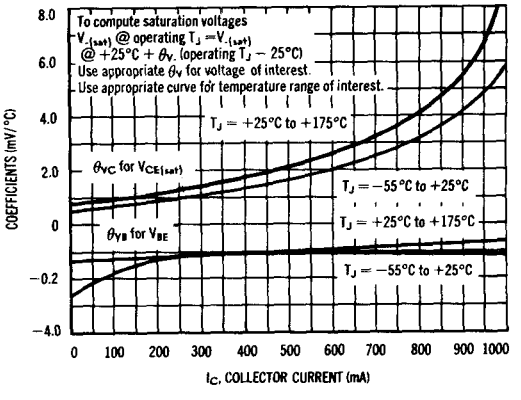
COLLECTOR SATURATION REGION



"ON" VOLTAGES



TEMPERATURE CO-EFFICIENTS

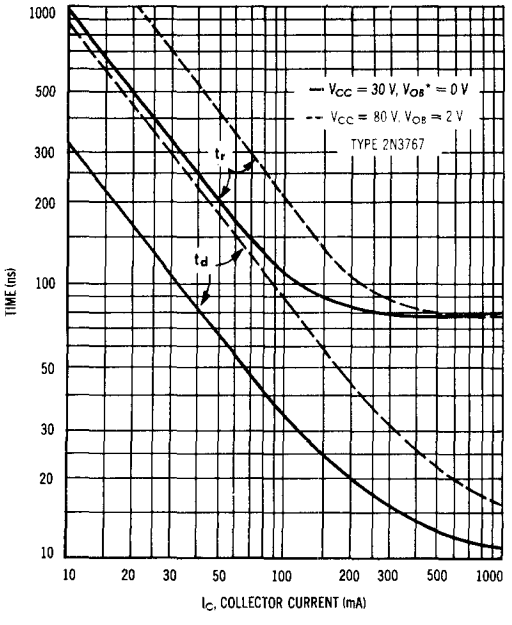


2N3766, 2N3767 (continued)

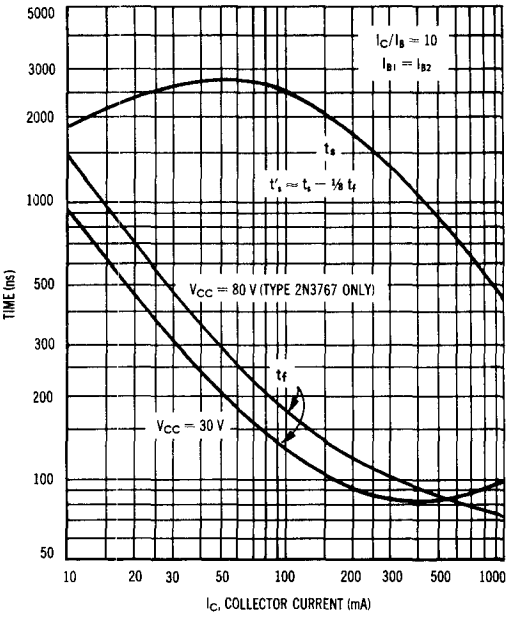
TRANSIENT CHARACTERISTICS

($T_J = 25°C$)

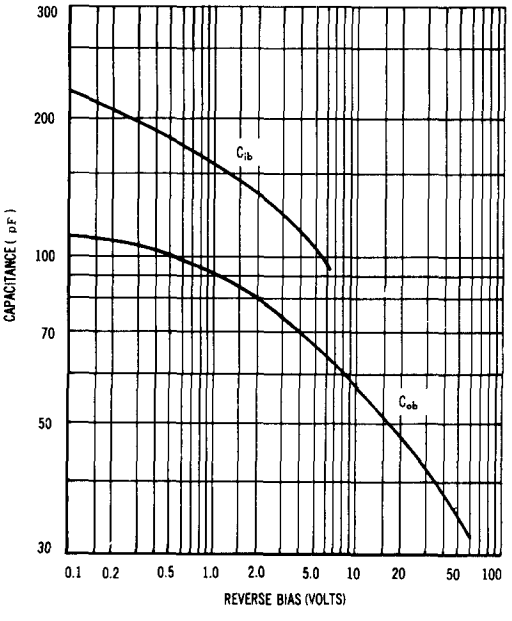
TURN-ON TIME



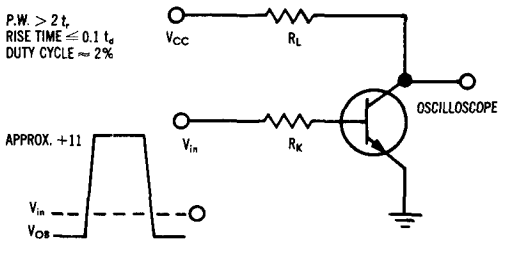
TURN-OFF TIME



CAPACITANCE

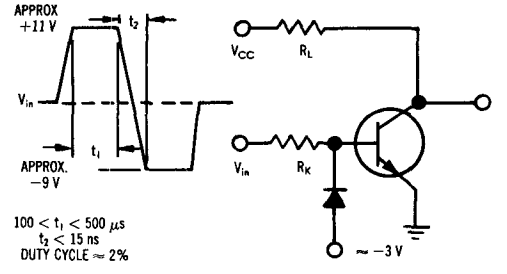


EQUIVALENT CIRCUIT FOR MEASURING DELAY AND RISE TIME



*V_{OB} = BASE-EMITTER "OFF" BIAS VOLTAGE

EQUIVALENT CIRCUIT FOR MEASURING STORAGE AND FALL TIMES



$100 < t_1 < 500\ \mu s$
$t_2 < 15$ ns
DUTY CYCLE ≈ 2%

2N3724, 2N3725 — 2N4013, 2N4014 (continued)

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS (continued)					
Collector-Emitter Saturation Voltage*		$V_{CE(sat)}$*			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)			-	0.25	
(I_C = 100 mAdc, I_B = 10 mAdc)	2N3724, 2N4013		-	0.20	
	2N3725, 2N4014		-	0.26	
(I_C = 300 mAdc, I_B = 30 mAdc)	2N3724, 2N4013		-	0.32	
	2N3725, 2N4014		-	0.40	
(I_C = 500 mAdc, I_B = 50 mAdc)	2N3724, 2N4013		-	0.42	
	2N3725, 2N4014		-	0.52	
(I_C = 800 mAdc, I_B = 80 mAdc)	2N3724, 2N4013		-	0.65	
	2N3725, 2N4014		-	0.80	
(I_C = 1.0 Adc, I_B = 100 mAdc)	2N3724, 2N4013		-	0.75	
	2N3725, 2N4014		-	0.95	
Base-Emitter Saturation Voltage*		$V_{BE(sat)}$*			Vdc
(I_C = 10 mAdc, I_B = 1.0 mAdc)			-	0.76	
(I_C = 100 mAdc, I_B = 10 mAdc)			-	0.86	
(I_C = 300 mAdc, I_B = 30 mAdc)			-	1.1	
(I_C = 500 mAdc, I_B = 50 mAdc)			0.9	1.2	
(I_C = 800 mAdc, I_B = 80 mAdc)			-	1.5	
(I_C = 1.0 Adc, I_B = 100 mAdc)			-	1.7	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain—Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)		f_T	300	-	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 140 kHz)	2N3724, 2N4013	C_{ob}	-	12	pF
	2N3725, 2N4014		-	10	
Input Capacitance (V_{BE} = 0.5 Vdc, I_C = 0, f = 140 kHz)		C_{ib}	-	55	pF
SWITCHING CHARACTERISTICS					
Turn-On Time	(V_{CC} = 30 Vdc, $V_{BE(off)}$ = 3.8 Vdc, I_C = 500 mAdc, I_{B1} = 50 mAdc) (See Figure 1)	t_{on}	-	35	ns
Delay Time		t_d	-	10	ns
Rise Time		t_r	-	30	ns
Turn-Off Time	(V_{CC} = 30 Vdc, I_C = 500 mAdc, I_{B1} = I_{B2} = 50 mAdc) (See Figure 1)	t_{off}	-	60	ns
Storage Time		t_s	-	50	ns
Fall Time	2N3724, 2N4013	t_f	-	25	ns
	2N3725, 2N4014		-	30	

* Pulse Test: Pulse Width = 300 μs, Duty Cycle = 1.0%.

FIGURE 1 — SWITCHING TIMES TEST CIRCUIT